

Tofiq Mammadov

List of Publications by Year in descending order

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47
papers

571
citations

623734

14
h-index

713466

21
g-index

47
all docs

47
docs citations

47
times ranked

142
citing authors

#	ARTICLE	IF	CITATIONS
1	Deformation effects in electronic spectra of the layered semiconductors TlGaS ₂ , TlGaSe ₂ and TlInS ₂ . Journal of Physics Condensed Matter, 2003, 15, 1291-1298.	1.8	32
2	Memory effect in ferroelectric-semiconductor with incommensurate phase TlGaSe ₂ . Solid State Communications, 2003, 128, 25-28.	1.9	31
3	Anomalous behaviour of the Urbach edge and phase transitions in TlGaSe ₂ . Solid State Communications, 1986, 58, 295-297.	1.9	28
4	Behavior of the layered crystals TlInS ₂ and TlGaSe ₂ near phase transitions in a static electric field. Low Temperature Physics, 2000, 26, 56-61.	0.6	28
5	The effect of impurities on the phase transitions in the ferroelectric semiconductors TlInS ₂ and TlGaSe ₂ . Journal of Physics Condensed Matter, 2005, 17, 1985-1993.	1.8	28
6	Phase transition and anisotropy of thermal expansion in TlInS ₂ . Solid State Communications, 1985, 53, 601-602.	1.9	24
7	Dielectric susceptibility behaviour in the incommensurate phase of TlInS ₂ . Physica B: Condensed Matter, 2003, 334, 13-20.	2.7	23
8	Phase transitions and metastable states in TlGaSe ₂ . Phase Transitions, 2003, 76, 1057-1064.	1.3	22
9	Neutron diffraction study of the crystal structure of TlInSe ₂ at high pressure. International Journal of Modern Physics B, 2019, 33, 1950149.	2.0	19
10	Structural phase transitions in Fe ³⁺ -doped ferroelectric TlGaSe ₂ crystal. Solid State Communications, 2008, 145, 539-544.	1.9	18
11	High Pressure Raman Study of Layered Semiconductor TlGaSe ₂ . Materials Science-Poland, 2018, 36, 203-208.	1.0	18
12	Negative thermal expansion in the layered semiconductor TlGaSe ₂ . Physica Status Solidi (B): Basic Research, 2005, 242, 983-989.	1.5	17
13	The Fundamental Absorption Edge of TlInSe ₂ . Physica Status Solidi (B): Basic Research, 1982, 113, K43.	1.5	16
14	Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of TlGaSe ₂ , TlGaS ₂ , and TlInS ₂ Crystals. Physica Status Solidi (B): Basic Research, 1985, 131, K23.	1.5	16
15	Thermal expansion of single crystals of the layered compounds TlGaSe ₂ and TlInS ₂ . Low Temperature Physics, 2001, 27, 676-680.	0.6	16
16	The Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of Crystals with TlSe ₂ Type Structure. Physica Status Solidi (B): Basic Research, 1984, 126, K139.	1.5	14
17	Time relaxation of dielectric constant in the commensurate phase of TlGaSe ₂ . Solid State Communications, 2004, 129, 761-764.	1.9	14
18	EPR spectra of Fe ³⁺ centers in layered TlGaSe ₂ single crystal. Solid State Communications, 2005, 133, 389-392.	1.9	14

#	ARTICLE	IF	CITATIONS
19	Effect of illumination on negative linear expansion of TlGaSe ₂ layered crystals. Journal of Physics and Chemistry of Solids, 2008, 69, 2544-2547.	4.0	13
20	Effect of external fields on the memory effect of the incommensurate phase in the ferroelectric-semiconductor TlGaSe ₂ . Physics of the Solid State, 2008, 50, 108-117.	0.6	13
21	Photodielectric effect in TlInS ₂ activated by the La impurity. Physics of the Solid State, 2009, 51, 264-269.	0.6	13
22	Identification of intrinsic deep level defects responsible for electret behavior in TlGaSe ₂ layered semiconductor. Physica B: Condensed Matter, 2016, 483, 82-89.	2.7	13
23	Photoelectric activity of structural defects of a single crystal of the ferroelectric-semiconductor TlInS ₂ : La. Physics of the Solid State, 2014, 56, 1605-1609.	0.6	12
24	The Fundamental Absorption Spectra of TlInSe ₂ Crystals Under Pressure. Physica Status Solidi (B): Basic Research, 1983, 117, K109.	1.5	9
25	Band Gap Variation in Mixed Crystals with TlSe ₂ Type Crystal Structure. Physica Status Solidi (B): Basic Research, 1988, 147, K99.	1.5	9
26	Preparation, crystal structure, and electrical properties of thallium monosulfide in the vicinity of high-temperature phase transitions. Physics of the Solid State, 2006, 48, 2322-2327.	0.6	9
27	Unusual memory effects in an incommensurate phase of the TlInS ₂ ferroelectric semiconductor. Physics of the Solid State, 2009, 51, 568-576.	0.6	9
28	Thermal history and dielectric behavior in the incommensurate phase of TlGaSe ₂ . Journal of Non-Crystalline Solids, 2005, 351, 2809-2812.	3.1	8
29	Pyroelectric properties and structural defects of a layered TlInS ₂ crystal doped with lanthanum. Physics of the Solid State, 2014, 56, 2028-2034.	0.6	8
30	Fundamental Absorption Edge of TlSe and TlInTe ₂ Crystals. Physica Status Solidi (B): Basic Research, 1985, 127, K55.	1.5	7
31	Phase transitions and polytypes in TlInS ₂ ferroelectric-semiconductor. Ferroelectrics, Letters Section, 1988, 8, 125-133.	1.0	7
32	Magnetic properties of Co implanted TlInS ₂ and TlGaSe ₂ crystals. Solid State Communications, 2012, 152, 407-409.	1.9	7
33	Photoelectric activity of defects in La-doped layered TlInS ₂ crystals. Low Temperature Physics, 2014, 40, 830-836.	0.6	7
34	Shift of the Fundamental Absorption Edge of TlSe Under Hydrostatic Pressure. Physica Status Solidi (B): Basic Research, 1982, 113, K127.	1.5	6
35	Thermal hysteresis and memory effects in TlGaSe ₂ crystal with incommensurate phase. Phase Transitions, 2005, 78, 413-419.	1.3	6
36	Phase transitions in the system of TlGa _{1-x} In _{1+x} Se ₂ S ₂ (1+x) solutions under hydrostatic pressure. Solid State Communications, 1985, 56, 989-993.	1.9	5

